TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16646FT

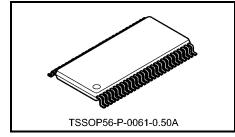
Low-Voltage 16-Bit Bus Transceiver/Register with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16646FT is a high-performance CMOS 16-bit bus transceiver/register. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V.$

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.25 g (typ.)

Features (Note)

- Low-voltage operation: VCC = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 2.9 \text{ ns (max)} (V_{CC} = 3.0 \text{ to } 3.6 \text{ V})$

 $: t_{pd} = 3.5 \text{ ns (max) (V}_{CC} = 2.3 \text{ to } 2.7 \text{ V})$

 $t_{pd} = 7.0 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$

- Output current: IOH/IOL = ±24 mA (min) (VCC = 3.0 V)
 - $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$
 - $: IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

Human body model ≥ ±2000 V

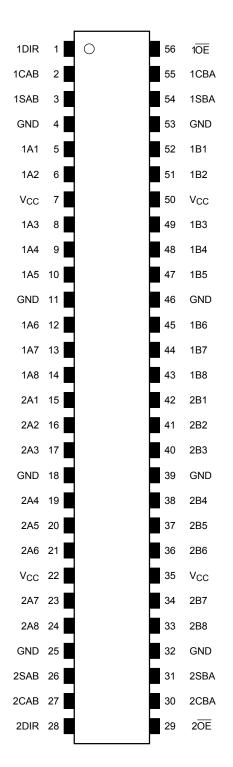
- Package: TSSOP
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

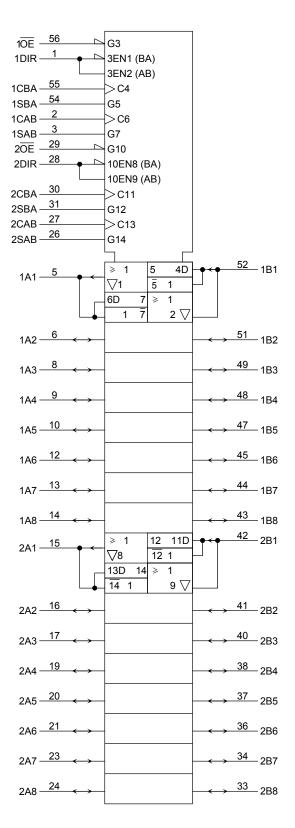
Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)

nt (top view) IEC Logic Symbol





2 2007-10-19



Truth Table

		Contro	I Inputs			В	us	- Function
ŌĒ	DIR	CAB	CBA	SAB	SBA	Α	В	Function
		X*	X*	Х	x x		Input	The output functions of A and B Busses are
	v	^*	^*	^	^	Z Z		disabled.
Н	Х			Х	Х	Х	X	Both A and B Busses are used as inputs to the internal flip-flops. Data on the Bus will be stored on the rising edge of the Clock.
						Input	Output	
		X*	X*	L	X	L	L	The data on the A bus are displayed on the B bus.
						Н	Н	
		$ \uparrow $	X*		Х	L	L	The data on the A bus are displayed on the
L	Н		^*	L	L X H		Н	B Bus, and are stored into the A storage flip-flops on the rising edge of CAB.
		X*	X*	Н	Х	х	Qn	The data in the A storage flop-flops are displayed on the B Bus.
		$\overline{}$					L	The data on the A Bus are stored into the A
			X*	Н	Х	Н	Н	storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B Bus.
						Output	Input	
		X*	X*	X	L	L	L	The data on the B Bus are displayed on the A bus.
						Н	Н	
		X*	_	Х		L	L	The data on the B Bus are displayed on the
L	L	^*		^	L	Н	Н	A Bus, and are stored into the B storage flip-flops on the rising edge of CBA.
		X*	X*	Х	Н	Qn	Х	The data in the B storage flip-flops are displayed on the A Bus.
			_			L	L	The data on the B Bus are stored into the B
		X*		Х	Н	Н	Н	storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A Bus.

X: Don't care

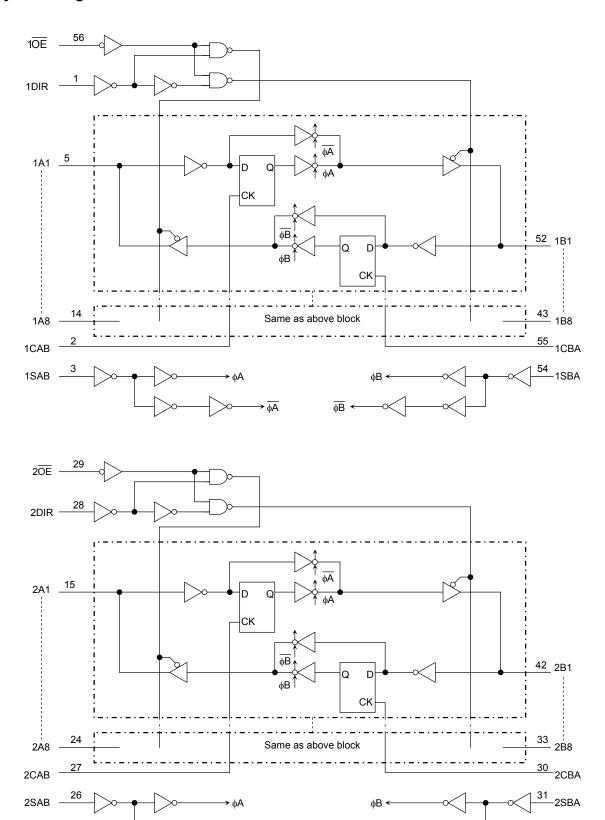
Z: High impedance

Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

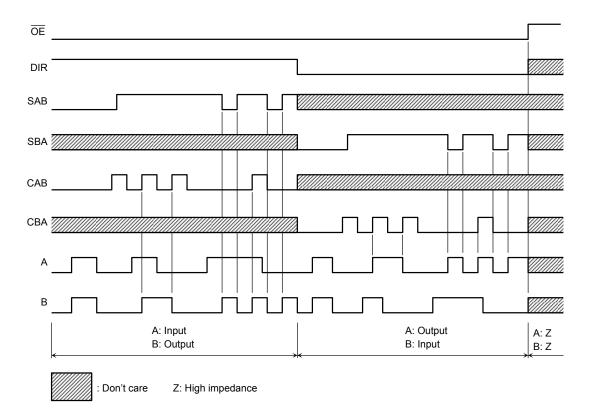
*: The clocks are not internally with either $\overline{\sf OE}$ or DIR.

Therefore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

System Diagram



Timing Chart



5 2007-10-19



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _C C	−0.5 to 4.6	V
DC input voltage (DIR, $\overline{\text{OE}}$, CAB, CBA, SAB, SBA)	V_{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC bus I/O voltage	V _{I/O}	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	l _{OUT}	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	Vcc	1.8 to 3.6	V	
Fower supply voltage	VCC	1.2 to 3.6 (Note 2)	V	
Input voltage (DIR, $\overline{\text{OE}}$, CAB, CBA, SAB, SBA)	V _{IN}	-0.3 to 3.6	V	
Bus I/O voltage	V _{I/O}	0 to 3.6 (Note 3)	V	
Bus I/O voltage	VI/O	0 to V _{CC} (Note 4)	v	
		±24 (Note 5)		
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA	
		±6 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{CC} \le 3.6$ V)

Characte	ristics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit
	H-level	V _{IH}	_		2.7 to 3.6	2.0	_	.,
Input voltage	L-level	V _{IL}		_	2.7 to 3.6	_	0.8	V
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				I _{OH} = -18 mA	3.0	2.4	_	
Output voltage				I _{OH} = -24 mA	3.0	2.2	_	V
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7 to 3.6	_	0.2	
	L-level	V _{OL}		I _{OL} = 12 mA	2.7	_	0.4	
	L-ievei			I _{OL} = 18 mA	3.0	_	0.4	
				$I_{OL} = 24 \text{ mA}$	3.0	_	0.55	
Input leakage curr	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μΑ
3-state output OFF state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		2.7 to 3.6	_	±10.0	μА
Power-off leakage current I _{OF}		l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ
Quiescent supply current		laa	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0	
Quiescent supply	Current	Icc	$V_{CC} \leqq (V_{IN},V_{OUT}) \leqq$	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		_	±20.0	μΑ
Increase in I _{CC} pe	r input	Δlcc	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteri	stics	Symbol			V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	-	_	2.3 to 2.7	1.6	_	V
Input voltage	L-level	VIL	-	_	2.3 to 2.7	_	0.7	V
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_	
	H-level	Voн	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.3	2.0	_	
				I _{OH} = -12 mA	2.3	1.8	_	V
Output voltage				$I_{OH} = -18 \text{ mA}$	2.3	1.7	_	
	L-level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \ \mu A$	2.3 to 2.7	_	0.2	
				$I_{OL} = 12 \text{ mA}$	2.3		0.4	
				$I_{OL} = 18 \text{ mA}$	2.3	_	0.6	
Input leakage curre	nt	I _{IN}	$V_{IN} = 0$ to 3.6 V		2.3 to 2.7		±5.0	μΑ
3-state output OFF state current		loz	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		2.3 to 2.7		±10.0	μА
Power-off leakage of	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Ovice cent comply of			V _{IN} = V _{CC} or GND		2.3 to 2.7	_	20.0	
Quiescent supply co	urrent	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.0$	6 V	2.3 to 2.7		±20.0	μА



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V $_{CC}$ < 2.3 V)

Characteris	stics	Symbol	Test Co	ondition	V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	_	_	1.8 to 2.3	0.7 × V _{CC}	_	V
Input voltage	L-level	V _{IL}	_	_	1.8 to 2.3	_	0.2 × V _{CC}	V
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{II}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage		011		I _{OH} = -6 mA	1.8	1.4	_	V
	L-level	Vai	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	_	0.2	
	L-level	rel V _{OL}	VIN = VIH OI VIL	I _{OL} = 6 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	$V_{IN} = 0$ to 3.6 V		1.8		±5.0	μΑ
3-state output OFF state current		loz	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	_	±10.0	μА
Power-off leakage current I _{OFF} V _{IN} , V _{OUT} = 0 to 3.6 V			0	_	10.0	μΑ		
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		1.8	_	20.0	μА
Quicacent supply co	mont	100	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6$	6 V	1.8	_	±20.0	μΛ



AC Characteristics (Ta = –40 to 85°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Test Condition		Min	Max	Unit
Characteriotics	Cymbol	Test container			Wida	Orme
			1.8	100		MHz
Maximum clock frequency	f _{max}	Figure 1, Figure 3	2.5 ± 0.2	200	_	
			3.3 ± 0.3	250	_	
Propagation delay time	4		1.8	1.5	7.0	
(An, Bn-Bn, An)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	3.5	ns
(All, bli-bli, All)	tpHL		3.3 ± 0.3	0.6	2.9	
Dranagation dalay time	4		1.8	1.5	8.8	
Propagation delay time (CAB, CBA-Bn, An)	t _{pLH}	Figure 1, Figure 3	2.5 ± 0.2	8.0	4.4	ns
(OAD, OBA-BII, AII)	tpHL		3.3 ± 0.3	0.6	3.2	
Drangation delay time			1.8	1.5	8.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.4	ns
(SAB, SBA-Bn, An)	tpHL		3.3 ± 0.3	0.6	3.5	
0.1.1.11.11	t _{pZL}		1.8	1.5	9.8	
Output enable time ($\overline{\sf OE}$, DIR-An, Bn)		Figure 1, Figure 4, Figure 5	2.5 ± 0.2	0.8	4.9	ns
(OE , DIR-AN, BN)			3.3 ± 0.3	0.6	3.8	
	t _{pLZ}		1.8	1.5	7.6	
Output disable time		Figure 1, Figure 4, Figure 5	2.5 ± 0.2	0.8	4.2	ns
($\overline{\sf OE}$, DIR-An, Bn)	t _{pHZ}		3.3 ± 0.3	0.6	3.7	
	1.		1.8	4.0	_	
Minimum pulse width	t _{w (H)}	Figure 1, Figure 3	2.5 ± 0.2	1.5	_	ns
	t _{w (L)}		3.3 ± 0.3	1.5	_	
			1.8	2.5		
Minimum setup time	t _s	Figure 1, Figure 3	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 3	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	t _{osLH}	(Note 2)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

Note 1: For $C_L = 50~pF$, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, \, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition				Unit	
Onaracteristics	Cymbol	rest domaillorr		V _{CC} (V)	Тур.	5	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	0.25		
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	0.6	V	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	8.0		
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	-0.25		
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	-0.6	V	
, 01		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	-0.8		
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	1.5		
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	1.9	٧	
, o		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	2.2		

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

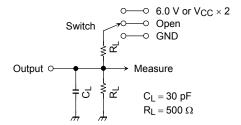
Characteristics	Symbol	Test Condition			Тур.	Unit
Onaracteristics	Cymbol	rest condition		V _{CC} (V)	ıyρ.	Offic
Input capacitance	C _{IN}	(DIR, $\overline{\text{OE}}$, CAB, CBA, SAB, SBA)		1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$	Note)	1.8, 2.5, 3.3	20	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC \text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V V _{CC} × 2		
t _{pHZ} , t _{pZH}		GND	

Figure 1

AC Waveform

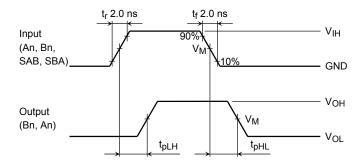


Figure 2 tpLH, tpHL

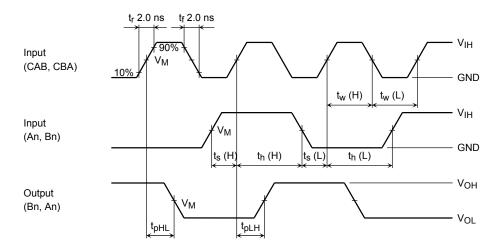


Figure 3 t_{pLH} , t_{pHL} , t_w , t_s , t_h

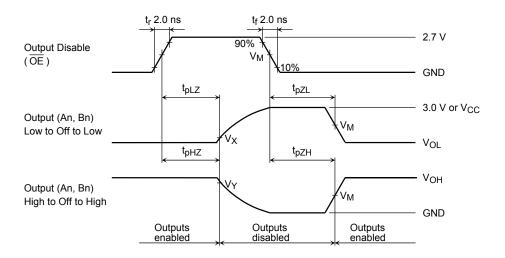


Figure 4 t_{pLZ} , t_{pH} , t_{pZ} , t_{pZH}

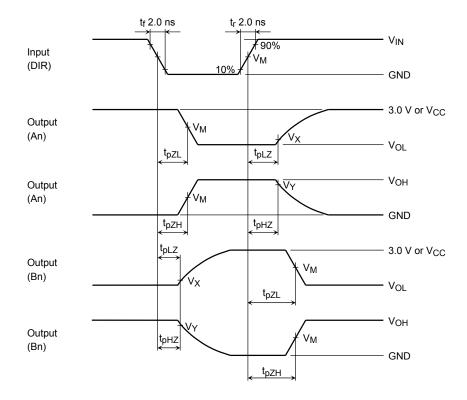


Figure 5 t_{pLZ} , t_{pH} , t_{pZ} , t_{pZH}

Symbol	V _{CC}								
Oymboi	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V						
V _{IH}	2.7 V	V _{CC}	V _{CC}						
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2						
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V						
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V						

12 2007-10-19

Package Dimensions

TSSOP56-P-0061-0.50A Unit: mm 6.1 ± 0.1 $0.2^{\,+0.07}_{\,-0.06}$ 0.5 0.25TYP **⊕**0.1**M** 14.3MAX (0.5)14.0±0.1 0.45~0.75 1.0±0.05 0.1 ± 0.05

Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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